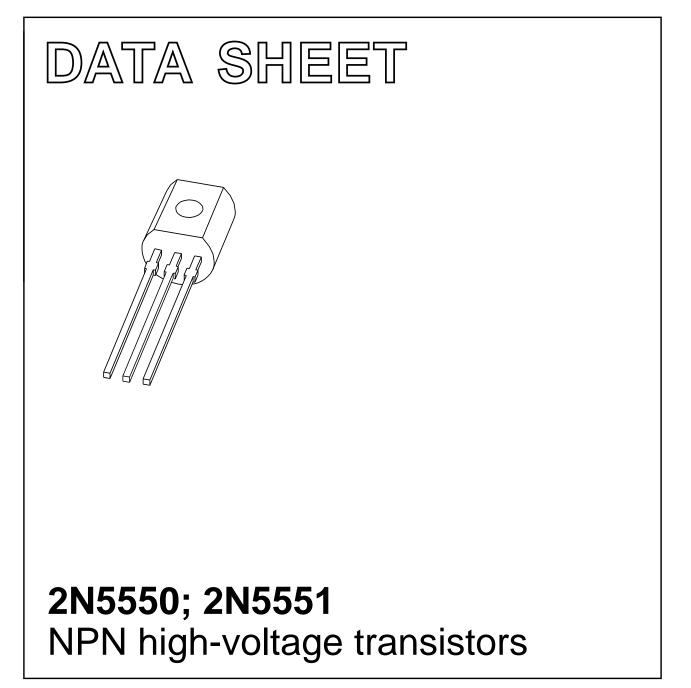
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 Apr 23 2004 Oct 28







FEATURES

• Low current (max. 300 mA)

• High voltage (max. 160 V).

APPLICATIONS

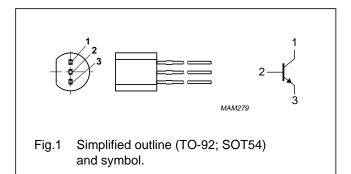
• Switching and amplification in high voltage applications such as telephony.

DESCRIPTION

NPN high-voltage transistor in a TO-92; SOT54 plastic package. PNP complements: 2N5400 and 2N5401.

PINNING

PIN	DESCRIPTION	
1	collector	
2	base	
3	emitter	



ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
	NAME	DESCRIPTION	VERSION	
2N5550	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54	
2N5551				

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	2N5550		_	160	V
	2N5551		-	180	V
V _{CEO}	collector-emitter voltage	open base			
	2N5550		_	140	V
	2N5551		_	160	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
Ic	collector current (DC)		-	300	mA
I _{CM}	peak collector current		-	600	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	630	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

2N5550; 2N5551

2N5550; 2N5551

THERMAL CHARACTERISTICS

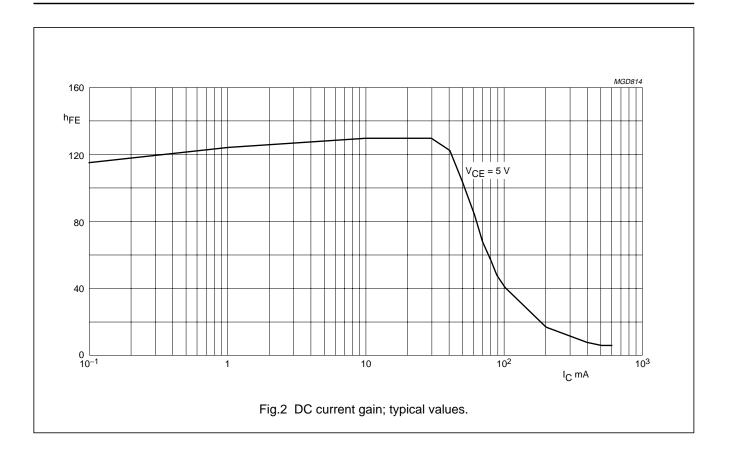
SYMBOL	PARAMETER	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	200	K/W

CHARACTERISTICS

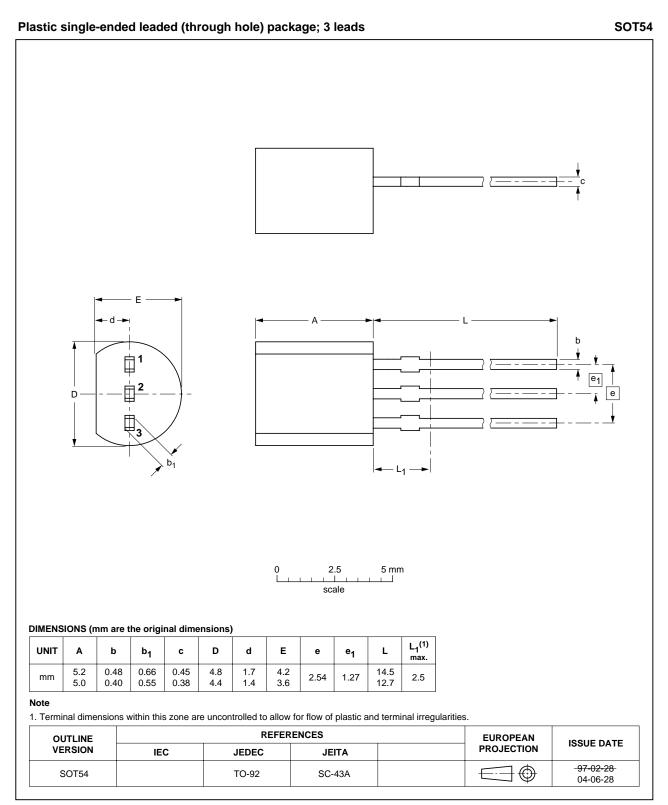
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current				
	2N5550	V _{CB} = 100 V; I _E = 0 A	_	100	nA
		V _{CB} = 100 V; I _E = 0 A; T _j = 100 °C	-	100	μA
	collector-base cut-off current				
	2N5551	V _{CB} = 120 V; I _E = 0 A	_	50	nA
		V _{CB} = 120 V; I _E = 0 A; T _i = 100 °C	_	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$	_	50	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 1 \text{ mA}; \text{ see Fig.2}$			
	2N5550		60	_	
	2N5551		80	_	
	DC current gain	$V_{CE} = 5 V; I_{C} = 10 mA; see Fig.2$			
	2N5550		60	250	
	2N5551		80	250	
	DC current gain	$V_{CE} = 5 V; I_{C} = 50 mA; see Fig.2$			
	2N5550		20	_	
	2N5551		30	_	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = 10 \text{ mA}; I_{\rm B} = 1 \text{ mA}$			
	2N5550		_	150	mV
	2N5551		_	150	mV
	collector-emitter saturation voltage	$I_{\rm C} = 50 \text{ mA}; I_{\rm B} = 5 \text{ mA}$			
	2N5550		_	250	mV
	2N5551		_	200	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	_	1	V
22000		$I_{\rm C} = 50 \text{ mA}; I_{\rm B} = 5 \text{ mA}$	_	1	V
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; \text{ I}_{\text{E}} = \text{i}_{\text{e}} = 0 \text{ A}; \text{ f} = 1 \text{ MHz}$	_	6	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$	_	30	pF
f _T	transition frequency	V _{CE} = 10 V; I _C = 10 mA; f = 100 MHz	100	300	MHz
F	noise figure	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 200 \mu\text{A}; \text{ R}_{S} = 2 k\Omega;$			1
	2N5550	f = 10 Hz to 15.7 kHz	_	10	dB
	2N5551		_	8	dB

2N5550; 2N5551



PACKAGE OUTLINE



2N5550; 2N5551

2N5550; 2N5551

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
1	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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